

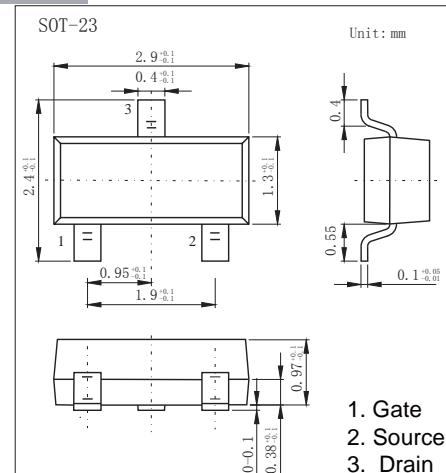
SOT-23 Plastic-Encapsulate MOSFETS

Features

- VDS (V) = -20V
- RDS(ON)<0.052 Ω (VGS = -4.5V)
- RDS(ON)<0.071 Ω (VGS = -2.5V)
- RDS(ON)<0.108 Ω (VGS = -1.8V)
- P-Channel MOSFET

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-source voltage Gate-source voltage	V _{DSS} V _{GSS}	-20 ±10	V V
Continuous drain current TA=25°C TA=70°C	I _D	-3.5 -2.8	A
Pulsed drain current	I _{DM}	-12	A
Power dissipation TA=25°C TA=70°C	P _D	1.25 0.8	W
Thermal Resistance Junction-to-Ambient	R _{θJA}	130	°C/W
Operating junction and storage temperature range	T _j , T _{stg}	-55 to +150	°C

MOSFET ELECTRICAL CHARACTERISTICS Ta=25 °C unless otherwise specified

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	V _{DSS}	V _{GS} = 0 V, I _D = -250 μA	-20			V
Gate threshold voltage	V _{GSS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.45		-0.8	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -20V , V _{GS} = 0 V, T _J = 55 °C			-10	
Gate-body leakage	I _{GS}	V _{DS} = 0 V, V _{GS} = ±10 V			±100	nA
Drain-source on-state resistance	R _{D(on)}	V _{GS} = -4.5 V, I _D = -3.5 A	0.044	0.052		
		V _{GS} = -2.5 V, I _D = -3.0 A	0.060	0.071		Ω
		V _{GS} = -2 V , I _D = -2.0 A	0.087	0.108		
On-state drain current	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-6			A
		V _{DS} ≤ -5 V, V _{GS} = -2.5 V	-3			
Forward transconductance	g _f s	V _{DS} = -5 V, I _D = -3.5 A		8.5		S
Input capacitance *	C _{iss}			1245		
Output capacitance *	C _{oss}	V _{DS} = -10V , V _{GS} = 0 , f = 1 MHz		375		pF
Reverse transfer capacitance *	C _{rss}			210		
Total gate charge *	Q _g			10	15	
Gate-source charge *	Q _{gs}	V _{DS} = -10V , V _{GS} = -4.5 V , I _D = -3.5 A		2		nC
Gate-drain charge *	Q _{gd}			2		
Turn-on Delay time	t _{d(on)}			13	20	
Turn-on Reise time	t _r	V _{DD} = -5V , R _L = 4Ω , I _D = -1A , V _{GEN} = -4.5V , R _G = 6Ω		25	40	
Turn-off Dealy time	t _{d(off)}			55	80	
Turn-off Fall time	t _f			19	35	
Continuous source current (diode conduction) *	I _S			-1.6		A
Diode forward voltage	V _{SD}	I _S = -1.6 A, V _{GS} = 0 V			-1.2	V

* Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.

Marking	A5
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